

ARTICLES

Effects of dopant ion and Mn valence state in the $\text{La}_{1-x}\text{A}_x\text{MnO}_3$ ($\text{A} = \text{Sr}, \text{Ba}$) colossal magnetoresistance films

Sun Gyu Choi, Seok-Joo Wang, Hyung-Ho Park, MunPyo Hong and Kwang-Ho Kwon
J. Vac. Sci. Technol. A **28**, 1 (2010); <http://dx.doi.org/10.1116/1.3256197>

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Study of $\text{Ni}_2\text{-Mn-Ga}$ phase formation by magnetron sputtering film deposition at low temperature onto Si substrates and $\text{LaNiO}_3/\text{Pb}(\text{Ti}, \text{Zr})\text{O}_3$ buffer

F. Figueiras, E. Rauwel, V. S. Amaral, N. Vyshatko, A. L. Khoklin, C. Soyer, D. Remiens, V. V. Shvartsman, P. Borisov and W. Kleemann
J. Vac. Sci. Technol. A **28**, 6 (2010); <http://dx.doi.org/10.1116/1.3256200>

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Etching characteristics and mechanism of indium tin oxide films in an inductively coupled HBr/Ar plasma

Kwang-Ho Kwon, Alexander Efremov, Yong-Hyun Ham, Nam Ki Min, Hyun Woo Lee, Mun Pyo Hong and Kwangsoo Kim
J. Vac. Sci. Technol. A **28**, 11 (2010); <http://dx.doi.org/10.1116/1.3256226>

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Effects of Al doping and annealing on chemical states and band diagram of $\text{Y}_2\text{O}_3/\text{Si}$ gate stacks studied by photoemission and x-ray absorption spectroscopy

Satoshi Toyoda, Jun Okabayashi, Makoto Komatsu, Masaharu Oshima, Dong-Ick Lee, Shiyu Sun, Yun Sun, Piero A. Pianetta, Dmitry Kukuruznyak and Toyohiro Chikyow
J. Vac. Sci. Technol. A **28**, 16 (2010); <http://dx.doi.org/10.1116/1.3259869>

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***In situ* x-ray diffraction study of Ni-Yb interlayer and alloy systems on Si(100)**

W. Knaepen, J. Demeulemeester, J. Jordan-Sweet, A. Vantomme, C. Detavernier, R. L. Van Meirhaeghe and C. Lavoie
J. Vac. Sci. Technol. A **28**, 20 (2010); <http://dx.doi.org/10.1116/1.3259875>

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Effect of methane addition on ultrananocrystalline diamond formation: Morphology changes and induced stress

S. C. Ramos, A. F. Azevedo, M. R. Baldan and N. G. Ferreira
J. Vac. Sci. Technol. A **28**, 27 (2010); <http://dx.doi.org/10.1116/1.3259885>

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Microstructure and temperature coefficient of resistance of thin cermet resistor films deposited from $\text{CrSi}_2\text{-Cr-SiC}$ targets by S-gun magnetron

Valery V. Felmetsger
J. Vac. Sci. Technol. A **28**, 33 (2010); <http://dx.doi.org/10.1116/1.3259847>

[+ VIEW DESCRIPTION](#)**Flexible indium zinc oxide/Ag/indium zinc oxide multilayer electrode grown on polyethersulfone substrate by cost-efficient roll-to-roll sputtering for flexible organic photovoltaics**

Yong-Seok Park and Han-Ki Kim

J. Vac. Sci. Technol. A **28**, 41 (2010); <http://dx.doi.org/10.1116/1.3264464>[+ VIEW DESCRIPTION](#)**Influence of annealing and Ag doping on structural and optical properties of indium tin oxide thin films**

Chun-Bin Cao, Lei Xiao, Xue-Ping Song and Zhao-Qi Sun

J. Vac. Sci. Technol. A **28**, 48 (2010); <http://dx.doi.org/10.1116/1.3264478>[+ VIEW DESCRIPTION](#)**Nanocrystalline cobalt-based films with high thermal stability from a single molecule**

Lucas B. Henderson, Joseph H. Rivers, Daniel E. Bost, Richard A. Jones and John G.

Ekerdt

J. Vac. Sci. Technol. A **28**, 54 (2010); <http://dx.doi.org/10.1116/1.3264480>[+ VIEW DESCRIPTION](#)**Effect of anion-to-cation supplying ratio on the surface morphology of AlN films grown on ZnO substrates at low temperature**

Inho Im, Mina Jung, Jieun Koo, Hyunjae Lee, Jinsub Park, Tsutomu Minegishi, Seunghwan

Park, Katsushi Fujii, Takafumi Yao, Gyungsuk Kil, Takashi Hanada and Jiho Chang

J. Vac. Sci. Technol. A **28**, 61 (2010); <http://dx.doi.org/10.1116/1.3264479>[+ VIEW DESCRIPTION](#)**Highly selective etching of silicon nitride to physical-vapor-deposited a-C mask in dual-frequency capacitively coupled CH₂F₂/H₂ plasmas**

J. S. Kim, B. S. Kwon, W. Heo, C. R. Jung, J. S. Park, J. W. Shon and N.-E. Lee

J. Vac. Sci. Technol. A **28**, 65 (2010); <http://dx.doi.org/10.1116/1.3268624>[+ VIEW DESCRIPTION](#)**Microstructure and chemical wet etching characteristics of AlN films deposited by ac reactive magnetron sputtering**

S. M. Tanner and V. V. Felmetser

J. Vac. Sci. Technol. A **28**, 69 (2010); <http://dx.doi.org/10.1116/1.3268620>[+ VIEW DESCRIPTION](#)**Optical emission spectroscopy as a tool for studying, optimizing, and monitoring plasma-assisted atomic layer deposition processes**

A. J. M. Mackus, S. B. S. Heil, E. Langereis, H. C. M. Knoops, M. C. M. van de Sanden and W.

M. M. Kessels

J. Vac. Sci. Technol. A **28**, 77 (2010); <http://dx.doi.org/10.1116/1.3256227>

[+ VIEW DESCRIPTION](#)**Influence of oxygen partial pressure on microstructure and discharge properties of Mg-Zr-O protective films deposited by magnetron sputtering**

Jianfeng Wang, Huiyan Wu, Zhongxiao Song, Yanhuai Li, Kewei Xu and Chunliang Liu
J. Vac. Sci. Technol. A **28**, 88 (2010); <http://dx.doi.org/10.1116/1.3259879>

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H. Shimizu, S. Shimada, S. Nagase, S. Muta and M. Ikeda
J. Vac. Sci. Technol. A **28**, 94 (2010); <http://dx.doi.org/10.1116/1.3259906>

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Katsuhiko Koike, Koichi Shimada and Shin Fukuda
J. Vac. Sci. Technol. A **28**, 99 (2010); <http://dx.doi.org/10.1116/1.3269736>

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W. P. Leroy, S. Mahieu, D. Depla and A. P. Ehiasarian
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[+ VIEW DESCRIPTION](#)***In situ* plasma diagnostics study of a commercial high-power hollow cathode magnetron deposition tool**

Liang Meng, Ramasamy Raju, Randolph Flauta, Hyungjoo Shin, David N. Ruzic and Douglas B. Hayden
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M.-P. Nghiem, Th. Tondu, J.-F. Roussel and D. Faye
J. Vac. Sci. Technol. A **28**, 119 (2010); <http://dx.doi.org/10.1116/1.3271134>

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Synthesis, characterization, and photoactivity of In Ta O₄ and In_{0.9}Ni_{0.1}Ta O₄ thin films prepared by electron evaporation

V. J. Rico, F. Frutos, F. Yubero, J. P. Espinos and A. R. González-Elipe
J. Vac. Sci. Technol. A **28**, 127 (2010); <http://dx.doi.org/10.1116/1.3273597>

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Crystallinity and resistivity of ZnO thin films with indium implantation and postannealing

Tokiyoshi Matsuda, Mamoru Furuta, Takahiro Hiramatsu, Hiroshi Furuta and Takashi Hirao
J. Vac. Sci. Technol. A **28**, 135 (2010); <http://dx.doi.org/10.1116/1.3259843>

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“SensArray” voltage sensor analysis in an inductively coupled plasma

M. J. Titus, C. C. Hsu and D. B. Graves
J. Vac. Sci. Technol. A **28**, 139 (2010); <http://dx.doi.org/10.1116/1.3268615>

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Influences of sulfur segregation to permeability in Pd-D₂ permeation system

J. S. Gao, T. Hioki, N. Takahashi and T. Motohiro
J. Vac. Sci. Technol. A **28**, 147 (2010); <http://dx.doi.org/10.1116/1.3273318>

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Position of segregated Al atoms and the work function: Experimental low energy electron diffraction intensity analysis and first-principles calculation of the ($\sqrt{3} \times \sqrt{3}$) R30° superlattice phase on the (111) surface of a Cu–9at.% Al alloy

M. Yoshitake, I. Karas, J. Houfek, S. Madeswaran, W. Song and V. Matolín
J. Vac. Sci. Technol. A **28**, 152 (2010); <http://dx.doi.org/10.1116/1.3273533>

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